

Notice of References Cited	Application/Control No. 10/634,001	Applicant(s)/Patent Under Reexamination CHANG ET AL.	
	Examiner Patricia A. George	Art Unit 1765	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,127,278	10-2000	Wang et al.	438/719
*	B	US-2003/0003748	01-2003	Khan et al.	438/694
*	C	US-5,665,203	09-1997	Lee et al.	438/585
*	D	US-6,284,665	09-2001	Lill et al.	438/710
	E	US-			
	F	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Westerheim et al. (High-density inductively coupled plasma etch of sub half micron critical layers: Transistor polysilicon gate definition and contact formation; American Vacuum Society Sept./Oct 1998, pg 2699-2706; Digital Semiconductor)
	V	Hwang et al. (Ion mass effect in plasma induced charging, June 1997; AIP).
	W	Wolf et al. (Silicon Processing for the VLSI Era; Vol. 1; 1986; Lattice Press)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.